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(54) SEMICONDUCTOR MEMORY DEVICE AND METHOD OF MANUFACTURING THE SEMICONDUCTOR MEMORY DEVICE

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(57) **ABSTRACT**

A semiconductor memory device, and a method of manufacturing the semiconductor memory device, includes a gate stack including interlayer insulating layers and word lines alternately stacked in a first direction, channel pillars passing through the gate stack and tapering toward the first direction, source select lines surrounding the channel pillars and extending to overlap the gate stack, and a source isolation insulating layer overlapping the gate stack between the source select lines and tapering toward a direction opposite to the first direction.

